

Notice of References Cited	Application/Control No. 10/791,417		Applicant(s)/Patent Under Reexamination TEOH ET AL.	
	Examiner Arpan P. Savla		Art Unit 2185	Page 1 of 1

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NON-PATENT DOCUMENTS

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	U	Lee et al. "Mobile Ion-Induced Data Retention Failure in NOR Flash Memory Cells", June 2001, IEE Transactions on Device and Materials Reliability, Vol. 1, No. 2, pp. 128-132. ✓
	V	Brand et al., "Novel Read Disturb Failure Mechanism Induced by FLASH Cycling", 1993, Reliability Physics Symposium, 31st Annual Proceedings, IEEE International, pp. 127-132. ✓
	W	Fastow et al., "Bake Induced Charge Gain in NOR Flash Cells", April 2000, IEEE Electronic Device Letters, Vol. 21, No. 4, pp. 184-186. ✓
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.